

**MOSFET – Single, P-Channel,
POWERTRENCH®**

FDN340P

FDN340P

TYPICAL CHARACTERISTICS

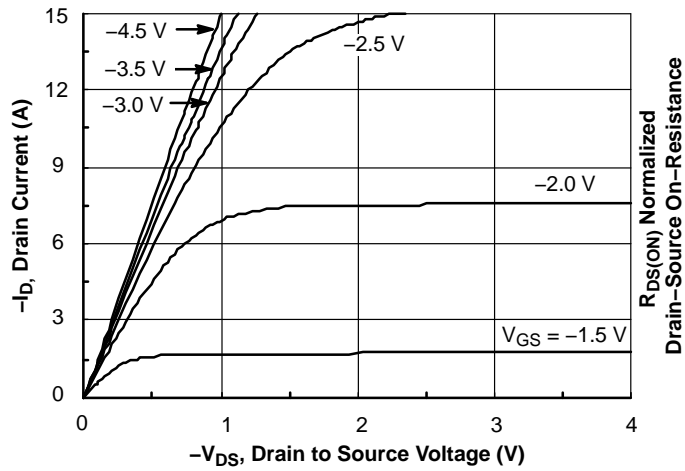


Figure 1. On-Region Characteristics

$R_{DS(ON)}$ Normalized
Drain-Source On-Resistance

$-I_D$, Drain Current (A)

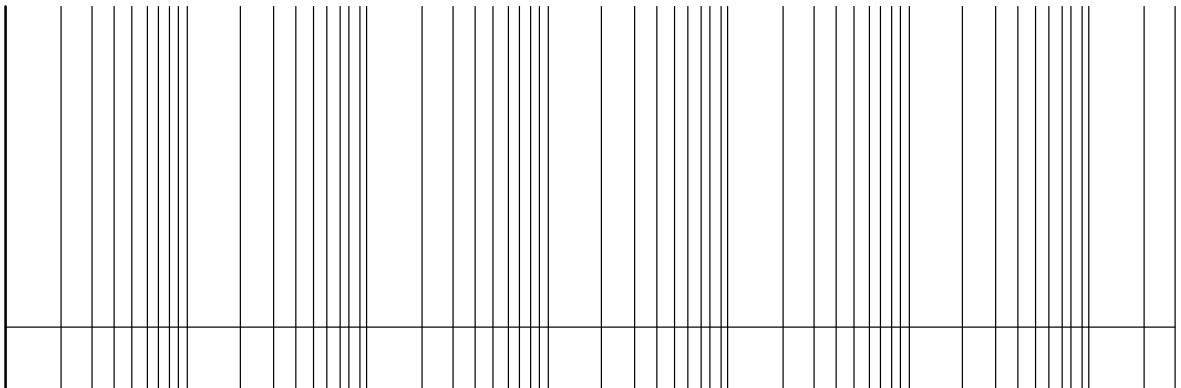
Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

Figure 3. On-Resistance Variation with Temperature

Figure 4. On-Resistance Variation with Gate-

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TYPICAL CHARACTERISTICS (Continued)



NOTE:

0.10

C

0.10 M C

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